



STL150N3LLH6

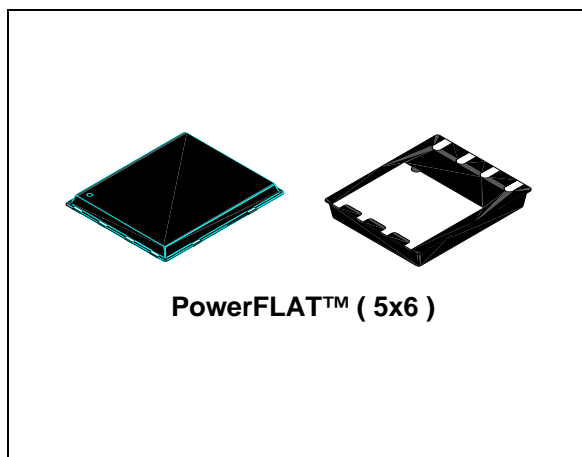
N-channel 30 V, 0.0016 Ω , 33 A PowerFLAT™ (5x6)
 STripFET™ VI DeepGATE™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on) max}	I _D
STL150N3LLH6	30 V	0.002 Ω	33 A ⁽¹⁾

1. The value is rated according R_{thj-pcb}

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- High avalanche ruggedness
- Low gate drive power losses
- Very low switching gate charge



Application

Switching applications

Description

The STL150N3LLH6 is a N-channel 30 V. This product utilizes the 6th generation of design rules of ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

Figure 1. Internal schematic diagram

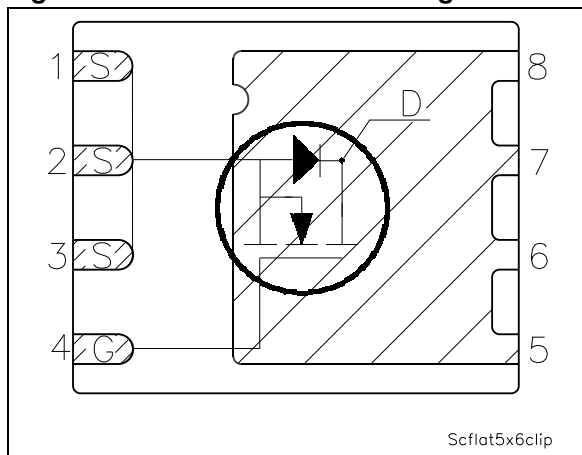


Table 1. Device summary

Order code	Marking	Package	Packaging
STL150N3LLH6	150N3LLH6	PowerFLAT™ (5x6)	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	150	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	93	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	33	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	20.8	A
$I_{DM}^{(3)}$	Drain current (pulsed)	132	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	80	W
$P_{TOT}^{(3)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	4	W
	Derating factor	0.03	W/ $^\circ\text{C}$
T_J	Operating junction temperature	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature		

1. The value is rated according R_{thj-c}
2. The value is rated according $R_{thj-pcb}$
3. Pulse width limited by safe operating area

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (drain) (steady state)	1.56	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient	31.3	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10$ sec

Table 4. Avalanche data

Symbol	Parameter	Value	Unit
I_{AV}	Not-repetitive avalanche current, (pulse width limited by T_J Max)	20	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$)	200	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating @ } 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 16.5\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 16.5\text{ A}$		0.0016 0.0025	0.002 0.0034	Ω Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	4040	-	pF
C_{oss}	Output capacitance			740		
C_{rss}	Reverse transfer capacitance			425		
Q_g	Total gate charge	$V_{DD} = 15\text{ V}$, $I_D = 33\text{ A}$ $V_{GS} = 4.5\text{ V}$ <i>(see Figure 14)</i>	-	40	-	nC
Q_{gs}	Gate-source charge			16.3		
Q_{gd}	Gate-drain charge			15.8		
R_G	Gate input resistance	$f = 1\text{ MHz}$ Gate DC Bias = 0 Test signal level = 20 mV open drain	-	1.4	-	Ω

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$t_{d(on)}$	Turn-on delay time	$V_{DD}=15\text{ V}$, $I_D=16.5\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 13)		17		ns	
t_r	Rise time			18		ns	
$t_{d(off)}$	Turn-off delay time				75		ns
t_f	Fall time				46		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
I_{SD}	Source-drain current		-		33	A	
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		132	A	
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=33\text{ A}$, $V_{GS}=0$	-		1.1	V	
t_{rr}	Reverse recovery time	$I_{SD}=33\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$, $V_{DD}=25\text{ V}$		34		ns	
Q_{rr}	Reverse recovery charge				35		nC
I_{RRM}	Reverse recovery current				2.1		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

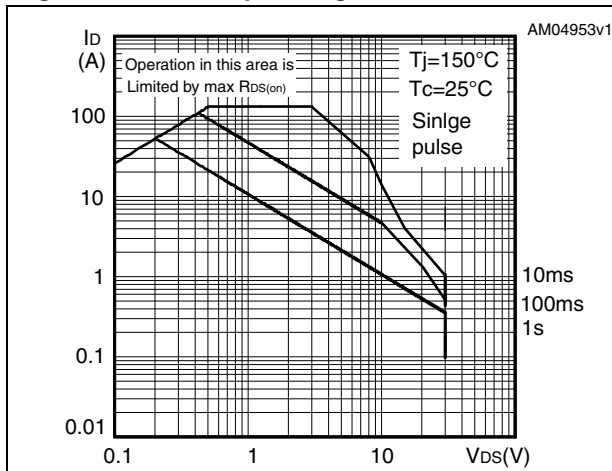


Figure 3. Thermal impedance

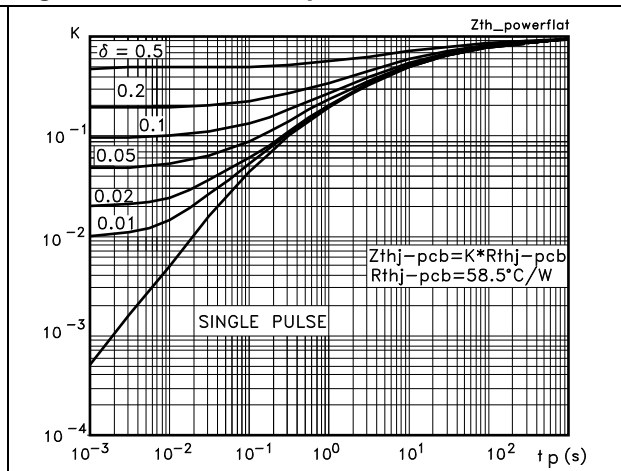


Figure 4. Output characteristics

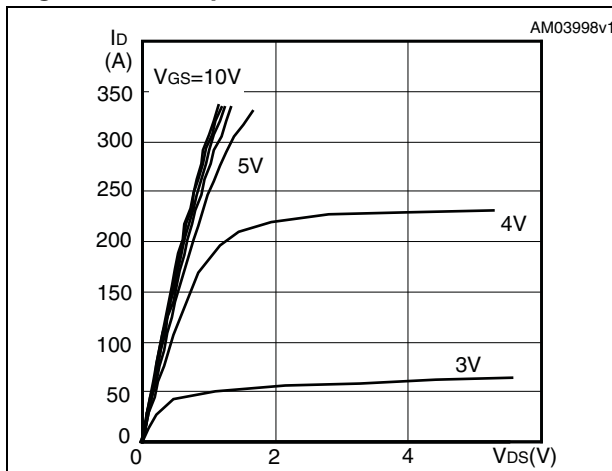


Figure 5. Transfer characteristics

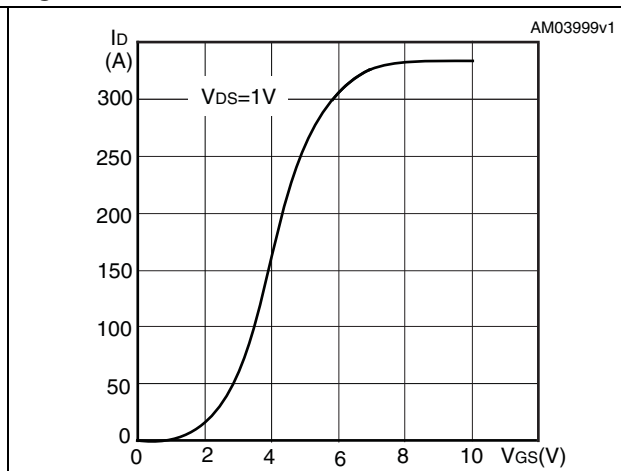


Figure 6. Normalized BV_{DSS} vs temperature

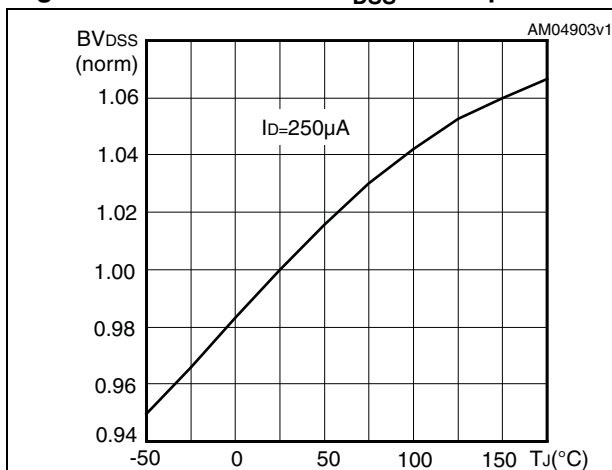


Figure 7. Static drain-source on resistance

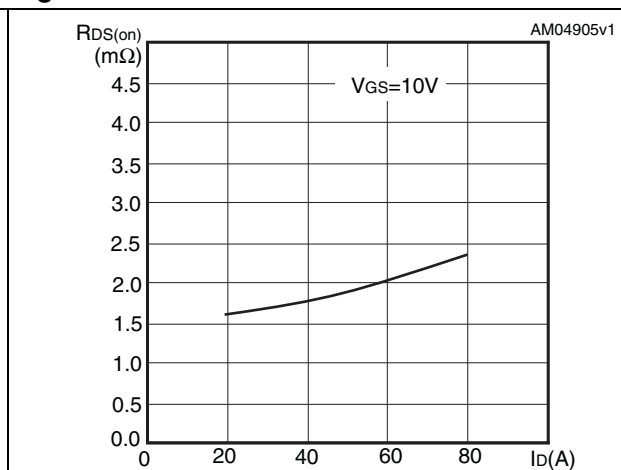


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

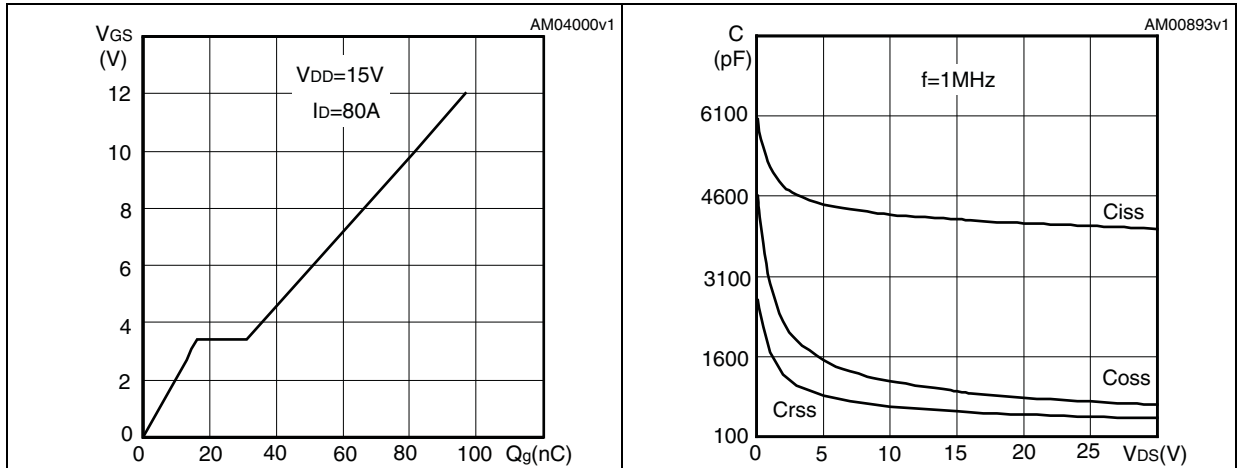


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

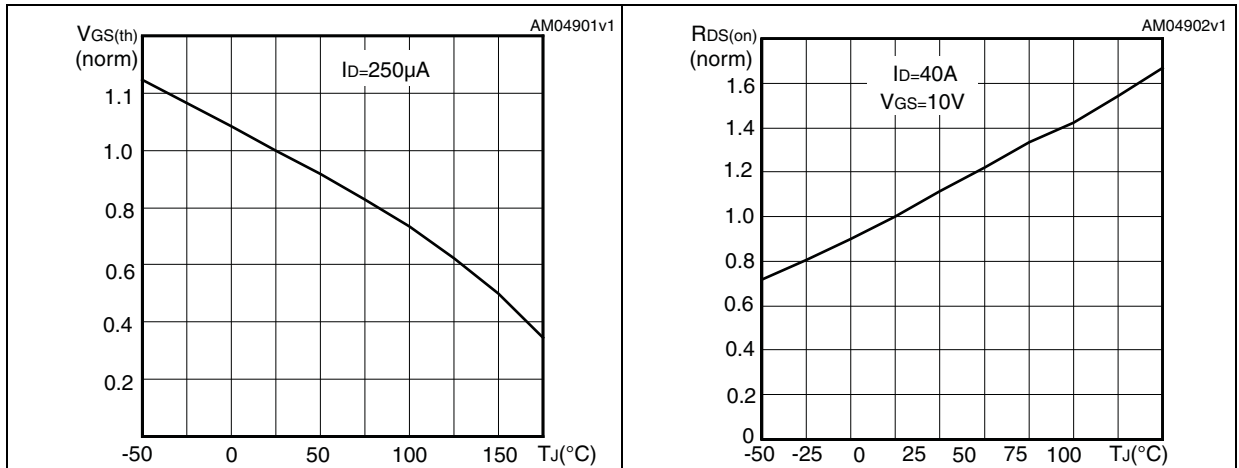
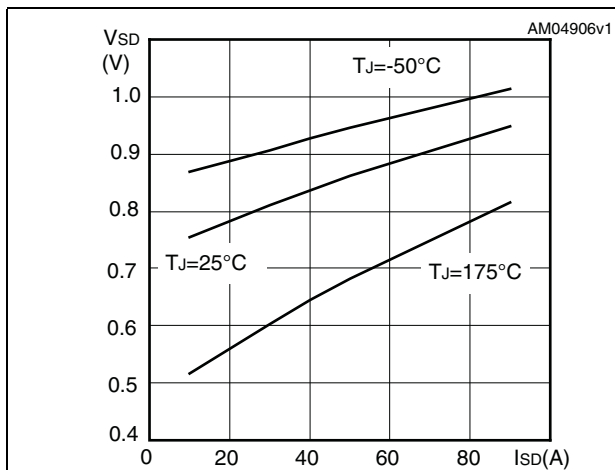
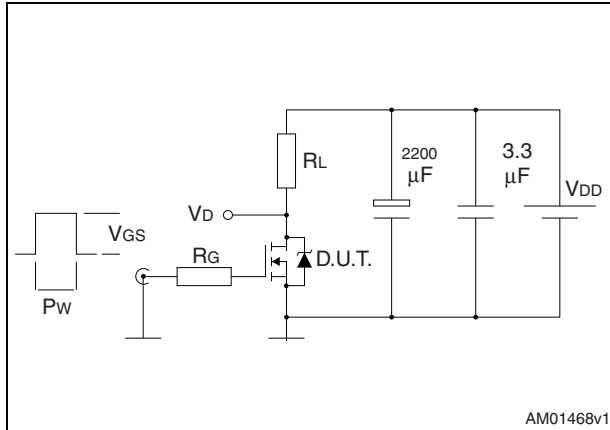


Figure 12. Source-drain diode forward characteristics



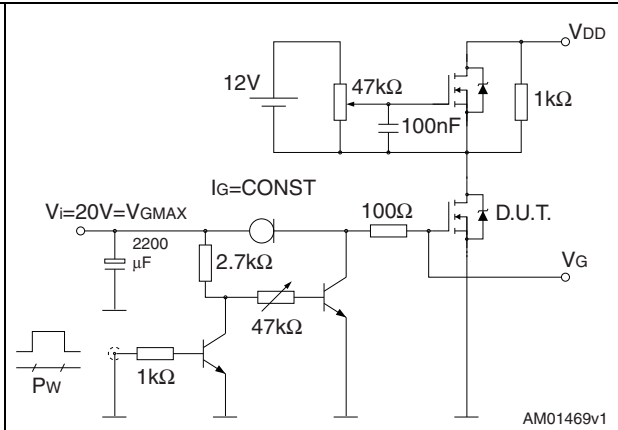
3 Test circuits

Figure 13. Switching times test circuit for resistive load



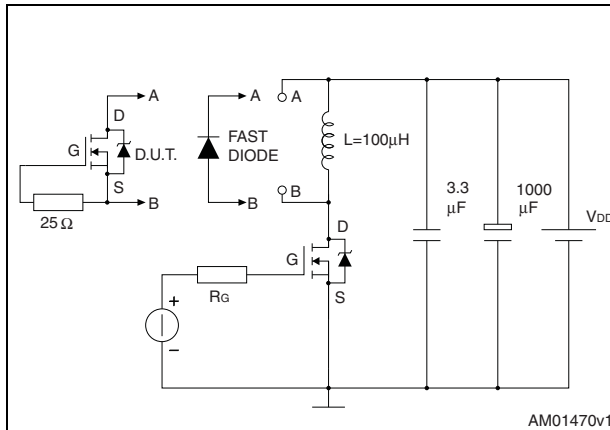
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Figure 14. Gate charge test circuit



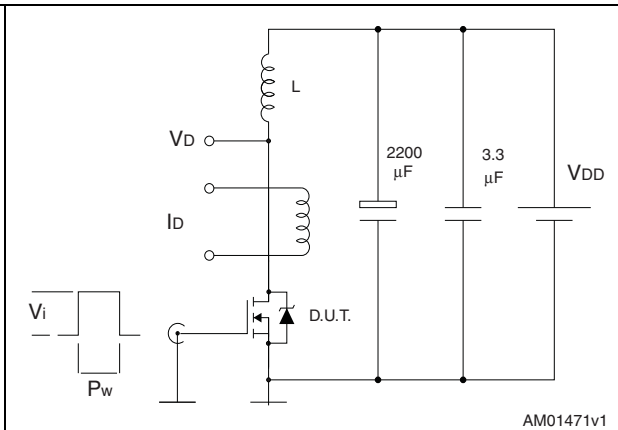
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Figure 15. Test circuit for inductive load switching and diode recovery times



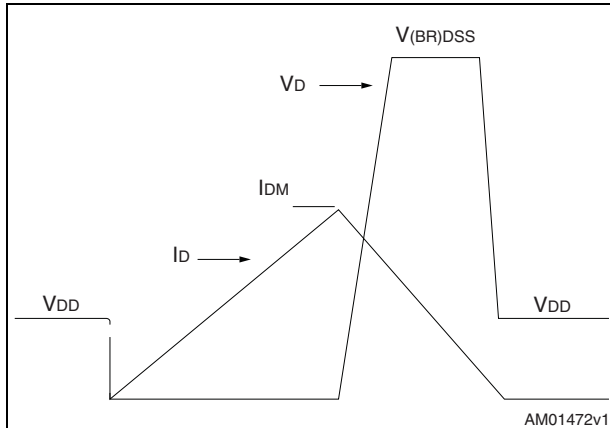
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Figure 16. Unclamped inductive load test circuit



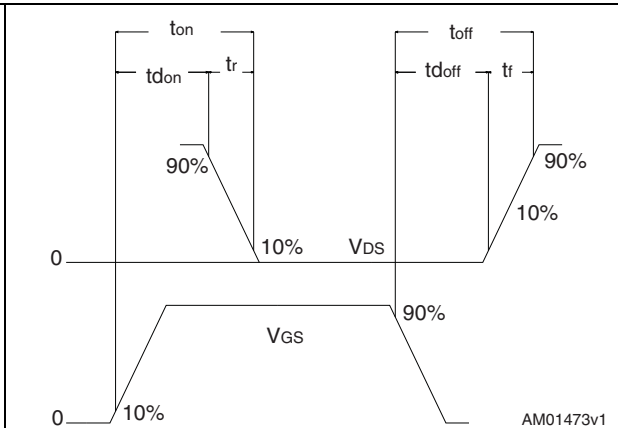
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Figure 17. Unclamped inductive waveform



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Figure 18. Switching time waveform



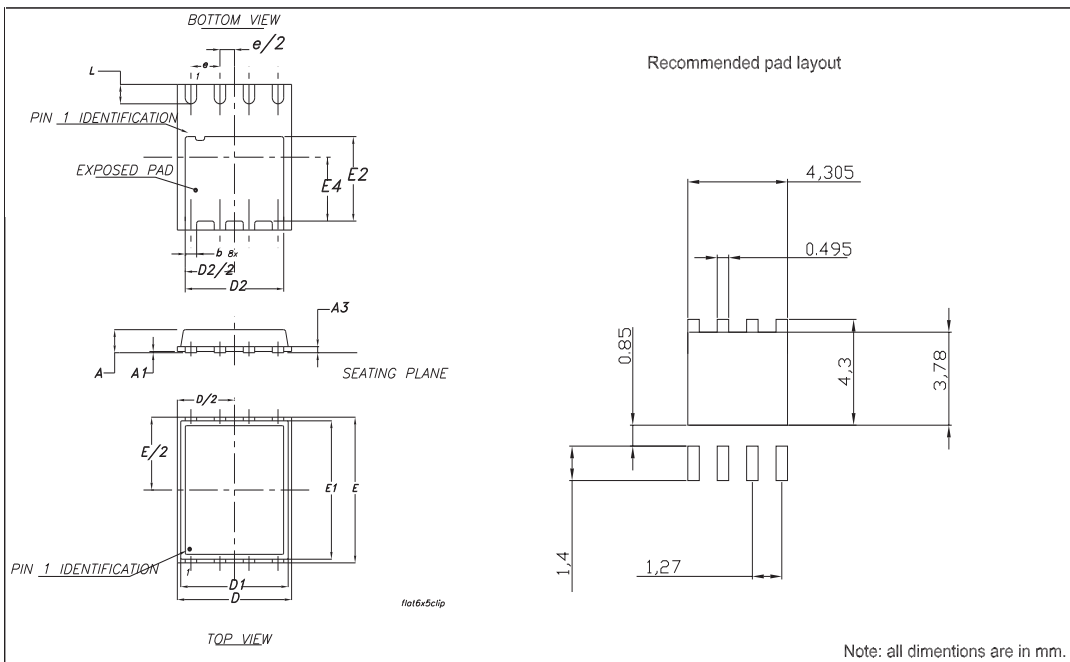
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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

PowerFLAT™ (5x6) mechanical data

DIM.	mm.			inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.80	0.83	0.93	0.031	0.32	0.036
A1		0.02	0.05		0.0007	0.0019
A3		0.20			0.007	
b	0.35	0.40	0.47	0.013	0.015	0.018
D		5.00			0.196	
D1		4.75			0.187	
D2	4.15	4.20	4.25	0.163	0.165	0.167
E		6.00			0.236	
E1		5.75			0.226	
E2	3.43	3.48	3.53	0.135	0.137	0.139
E4	2.58	2.63	2.68		0.103	0.105
e		1.27			0.050	
L	0.70	0.80	0.90	0.027	0.031	0.035



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
21-Jan-2009	1	First release
08-Sep-2009	2	Document status promoted from preliminary data to datasheet
11-Nov-2010	3	Corrected title in first page $R_{DS(on)}$ max value has been corrected.

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